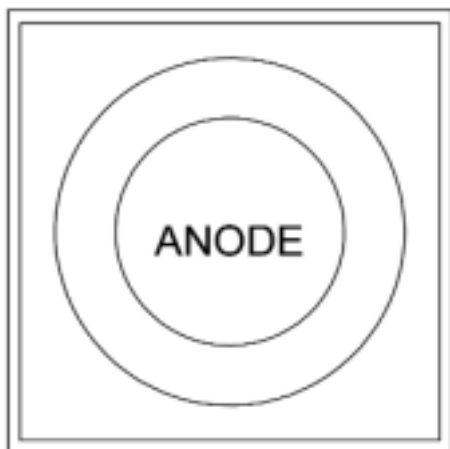


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	17.5 x 17.5 MILS
Die Thickness	8.0 MILS
Anode Bonding Pad Area	8.0 MILS DIAMETER
Top Side Metalization	Al - 15,000Å
Back Side Metalization	Au - 6,000Å

GEOMETRY



BACKSIDE CATHODE

PRINCIPAL DEVICE TYPES

CMPD2003
CMPD2004
1N3070

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